

Figure 1. Infrared absorbance change for the DMAI and H<sub>2</sub>O half-cycle during ALD of Al<sub>2</sub>O<sub>3</sub> on bare SiO<sub>2</sub> (10<sup>th</sup> cycle) and functionalized SiO<sub>2</sub> (10<sup>th</sup>, 30<sup>th</sup>, and 50<sup>th</sup> cycles).

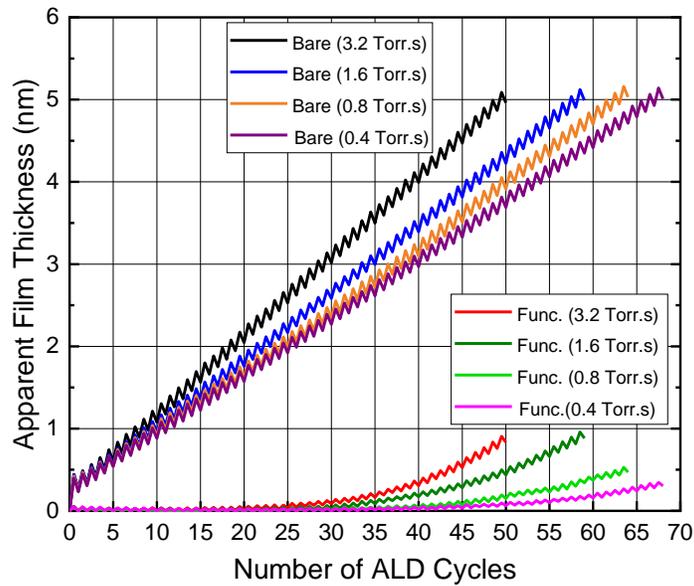


Figure 2. Apparent film thickness measured by *in situ* four-wavelength ellipsometry during deposition of Al<sub>2</sub>O<sub>3</sub> on bare SiO<sub>2</sub> and aminosilane-functionalized SiO<sub>2</sub> at different DMAI doses.